



浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

产品规格书

Specification of products

产品名称：可控硅模块

产品型号：SKKH273A16E-Y04

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ZHEJIANG SHILING SEMICONDUCTOR CO., LTD.

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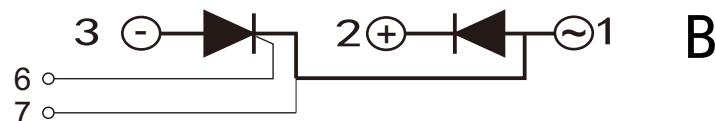
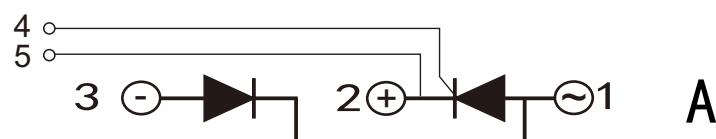
[Http://www.smrshiling.com](http://www.smrshiling.com)

| 拟制 | 审核 | 核准 |
|-----|-----|----|
| 林益龙 | 曹剑龙 | 宗瑞 |

| SYMBOL | CHARACTERISTIC | TEST CONDITIONS | T _J (°C) | | | | UNIT |
|--------------------------------------|--|---|---------------------|-----|------|-------|----------------------------------|
| | | | | Min | Type | Max | |
| I _{T(AV)} | Mean on-state current | 180° half sine wave 50Hz Single side cooled, T _c =85°C | 125 | | | 273 | A |
| I _{T(RMS)} | RMS on-state current | Single side cooled, T _c =85°C | 125 | | | 397 | A |
| V _{DRM} V _{RRM} | Repetitive peak off-state voltage Repetitive peak reverse voltage | V _{DRM} &V _{RRM} tp=10ms V _{DsM} &V _{RsM} = V _{DRM} &V _{RRM} +200V respectively | 125 | | 1600 | | V |
| I _{DRM} I _{RRM} | Repetitive peak current | at V _{DRM} at V _{RRM} | 125 | | | 30 | mA |
| I _{TSM} | Surge on-state current | 10ms half sine wave | 125 | | | 8.00 | KA |
| I ² t | I ² T for fusing coordination | V _R =60%V _{RRM} | | | | 320 | A ² s*10 ³ |
| V _{TO} | Threshold voltage | | 125 | | | 0.90 | V |
| r _T | On-state slop resistance | | | | | 0.45 | mΩ |
| V _{TM} | Peak on-state voltage | I _{TM} =750A | 25 | | | 1.50 | V |
| V _{FM} | Peak on-state voltage | I _{TM} =750A | 25 | | | 1.10 | V |
| dv/dt | Critical rate of rise of off-state voltage | V _{DM} =67%V _{DRM} | 125 | | | 1000 | V/μs |
| di/dt | Critical rate of rise of on-state current | From 67%V _{DRM} To 750A, Gate source 1.5A t _r ≤0.5 μs Repetitive | 125 | | | 130 | A/μs |
| I _{GT} | Gate trigger current | V _A =12V, I _A =1A | 25 | 30 | | 180 | mA |
| V _{GT} | Gate trigger voltage | | | 1.0 | | 2.5 | V |
| I _H | Holding current | | | 20 | | 100 | mA |
| V _{GD} | Non-trigger gate voltage | At 67%V _{DRM} | 125 | | | 0.2 | V |
| R _{th(j-c)} | Thermal resistance Junction to heatsink | At 180° sine Single side cooled | | | | 0.120 | °C/W |
| V _{iso} | Isolation voltage | 50Hz, RM. S, t=1min, I _{iso} : 1mA (MAX) | 2500 | | | | V |
| F _m | Thermal connection torque(M8) | | | | | 8.0 | N.m |
| | Mounting torque(M6) | | | | | 5.0 | N.m |
| T _{stg} | Stored temperature | | | -40 | | 150 | °C |
| W _t | Weight | | | | | 900 | g |
| Outline | | | | | | | |

OUTLINE DRAWING & CIRCUIT DIAGRAM

SKKH:



Rating and Characteristic

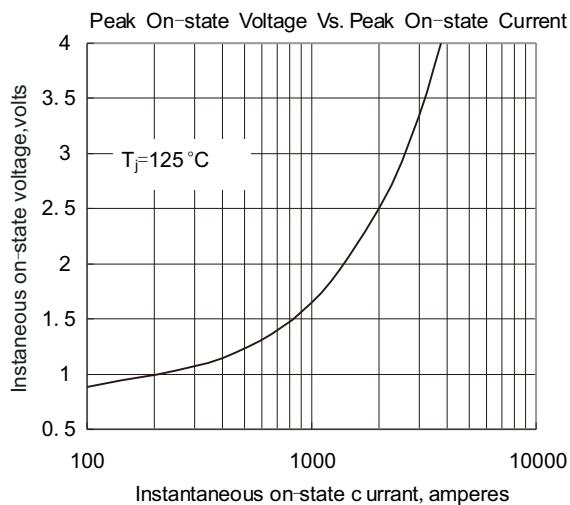


Fig.1

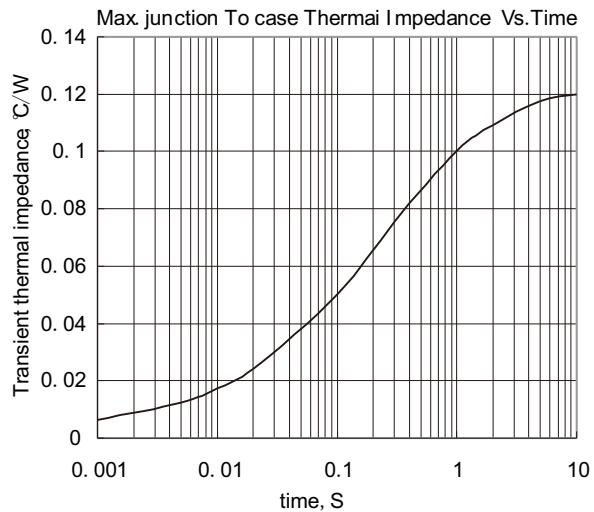


Fig. 2

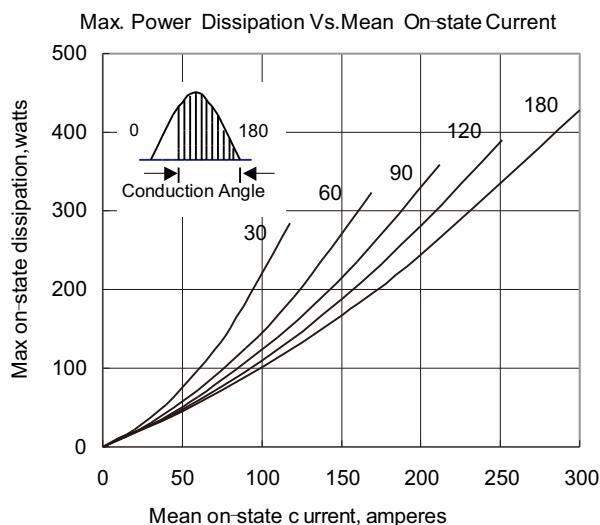


Fig.3

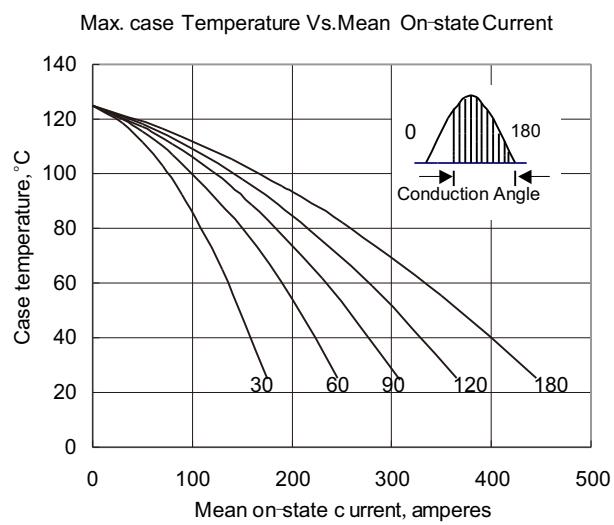


Fig.4

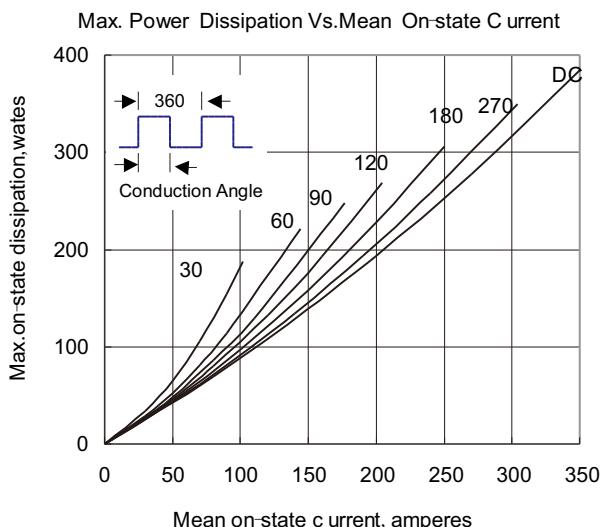


Fig.5

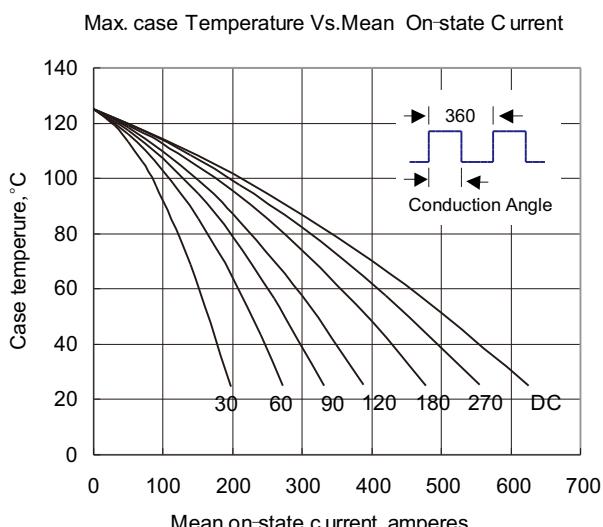


Fig.6

Rating and Characteristic

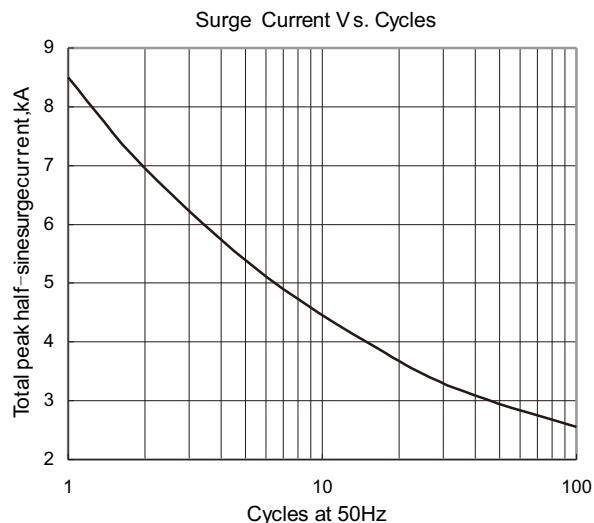


Fig. 7

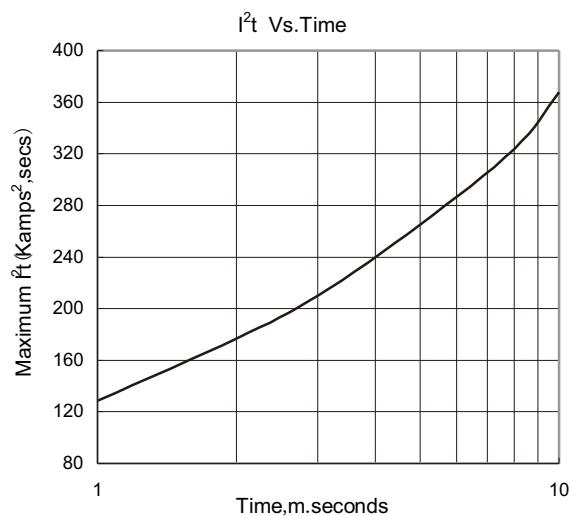


Fig. 8

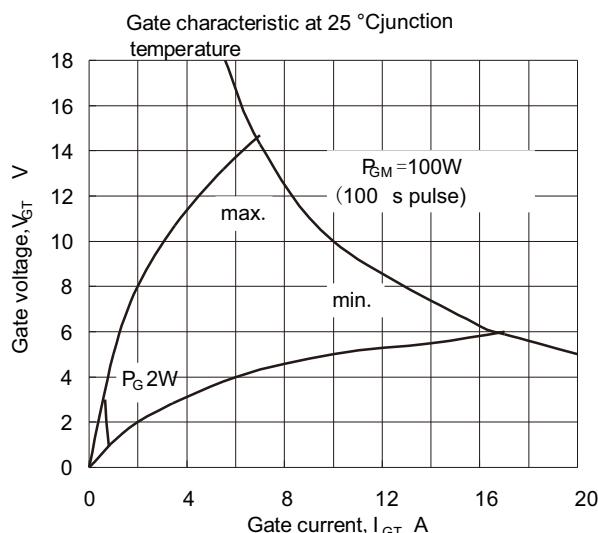


Fig. 9

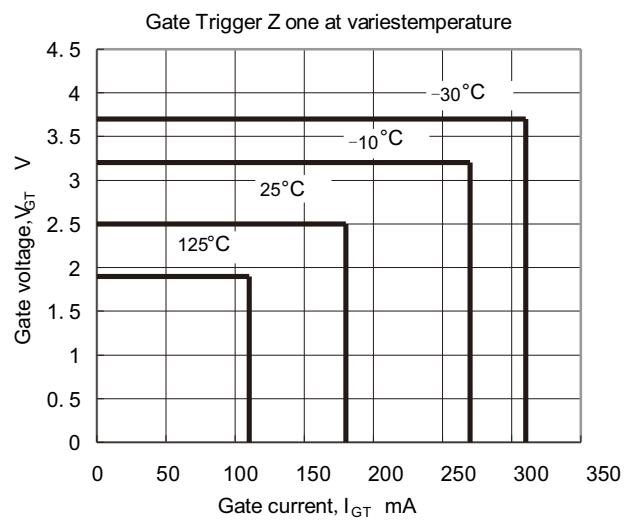


Fig. 10

Outside Dimension

